

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH3484 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=33m Ω (typ.)
- · 0.9V drive
- · Halogen free compliance

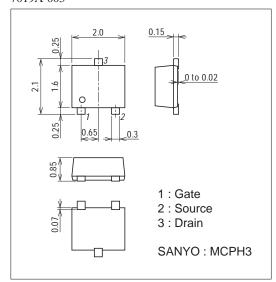
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	VGSS		±5	V
Drain Current (DC)	ID		4.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	18	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Operating Temperature	Topr		-5 to +150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7019A-003

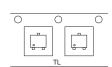


Product & Package Information

• Package : MCPH3

• JEITA, JEDEC : SC-70, SOT-323 • Minimum Packing Quantity : 3,000 pcs./reel

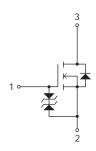
Packing Type: TL



Marking



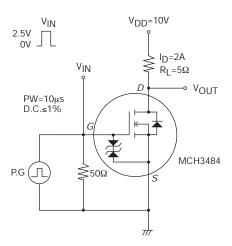
Electrical Connection

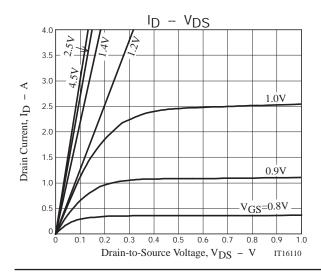


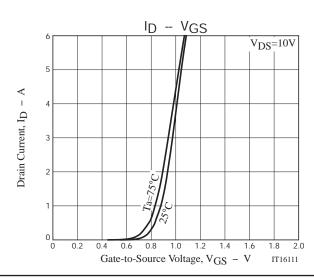
Electrical Characteristics at Ta=25°C

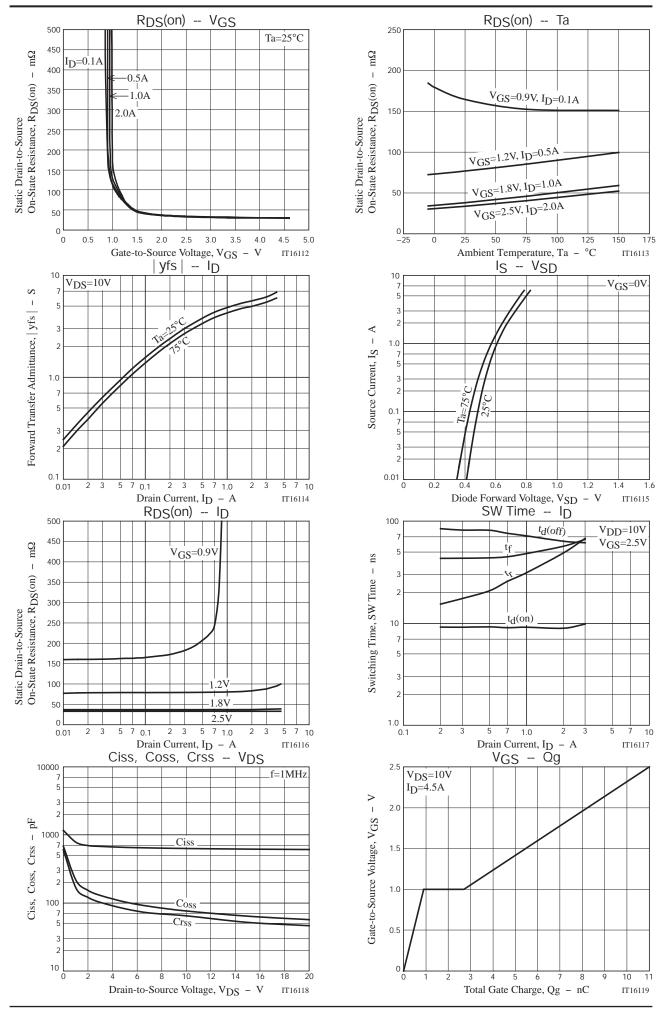
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±4V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.3		0.8	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A		5.6		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =2A, V _G S=2.5V		33	40	mΩ
	R _{DS} (on)2	I _D =1A, V _G S=1.8V		37	49	mΩ
	R _{DS} (on)3	I _D =0.5A, V _{GS} =1.2V		79	119	mΩ
	RDS(on)4	ID=0.1A, VGS=0.9V		165	330	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		630		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		75		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		65		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		8.9		ns
Rise Time	tr	See specified Test Circuit.		49		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		63		ns
Fall Time	tf	See specified Test Circuit.		57		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =2.5V, I _D =4.5A		11		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =2.5V, I _D =4.5A		0.9		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =2.5V, I _D =4.5A		1.8		nC
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.8	1.2	V

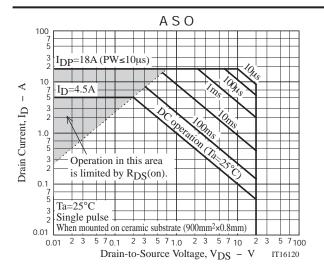
Switching Time Test Circuit

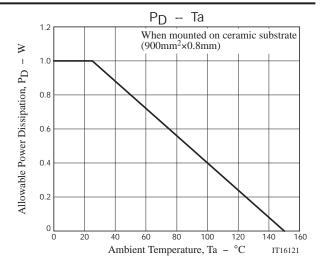












Note on usage: Since the MCH3484 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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